

DC-DC Resonant Converter

By Shalini Manna

3rd year,Electrical Engineering

Abstract: -

Power supplies are electrical circuits which convert a voltage at one level into a voltage at another level. It mainly comprises of a transformer, rectifier, filter, and regulator circuits. Every electronic application needs a supply foremost; or else there is simply no question of its functioning. Thus, power supplies and their evolving designs are always a necessity, and there is constant research into making it more efficient.

DC-DC Power converters are one kind of electrical power converters. It must have a low output impedance and stable voltage source. This project focuses on the Buck (step-down) converter topology.

This project was undertaken to study about resonant converters and the practical considerations in their fabrication, consequently making use of numerous software which are popularly used in the industry today.

Further research in this project could focus upon trying to establish multi-resonance in converters using inductors and capacitors. Also, a different design of the output filter inductor could be attempted.

Outline of Project :-

- Power circuit design as per specifications
- Magnetics – output filter inductor of power circuit
- Gate driver circuit design
- Controller design – closed loop voltage control
- PCB design

Problem Statement:-

Design and fabricate a closed loop 12 V to 5 V resonant buck converter with switching frequency 200 kHz in both zero-current switching and zero-voltage switching topologies.

1) Power Circuit:-

A buck converter is a DC-DC power converter which steps down voltage. It provides much higher power efficiency as compared to linear regulators, which dissipate power as heat but do not step up output current.

MOSFET used – **IRF640N** (Infineon Technologies N-channel MOSFET)

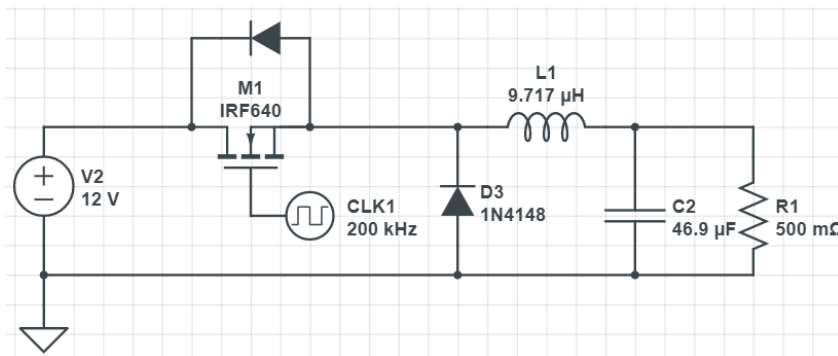


Figure 1: Buck converter power circuit

L1 and C2 form the output low pass filter which blocks the ac components of the switching frequency from reaching the output. Here the switching devices are a combination of a n-channel MOSFET and a diode, which makes a buck chopper specifically.

The following equations can be derived by using Volt-second balance and charge balance:-

- $V_o = V_g * D$
- $P_o = V_o * I_o$
- $\Delta I_l = \frac{(1-D)V_g(D)}{f * L}$
- $\Delta V_c = \frac{D(1-D)V_g}{8f^2 LC}$
- $I_{in} = \frac{P_{in}}{V_g}$
- $I_{d, avg} = (1 - D) * I_o$, Average diode current
- $I_{sw, rms} = \sqrt{D} * I_o$, RMS switch current
- $PIV = V_{in}$, (Peak Inverse Voltage of diode)

(Allowable capacitor voltage ripple is 1% of V_o)

(Inductor ripple current = 15% of I_o)

V_o = Output voltage

D = Duty cycle

V_g = Input voltage

I_o = Output current

ΔI_l = Inductor ripple current

ΔV_c = Capacitor voltage ripple

f_s = Switching frequency

I_{sw} = Switch current

P_{in} , P_o = Input, Output Power

$I_{sw, rms}$ = RMS Switch current

Calculated Values: -

$D = 0.416$ $P_o = 50 \text{ W}$ $\Delta I_l = 1.5 \text{ A}$ $\Delta V_c = 0.12 \text{ V}$ $I_{in} = 4.16 \text{ A}$
 $C = 562.6 \text{ uF}$ $L = 9.717 \text{ uH}$ $I_{d, avg} = 5.84 \text{ A}$

Simulation Results:-

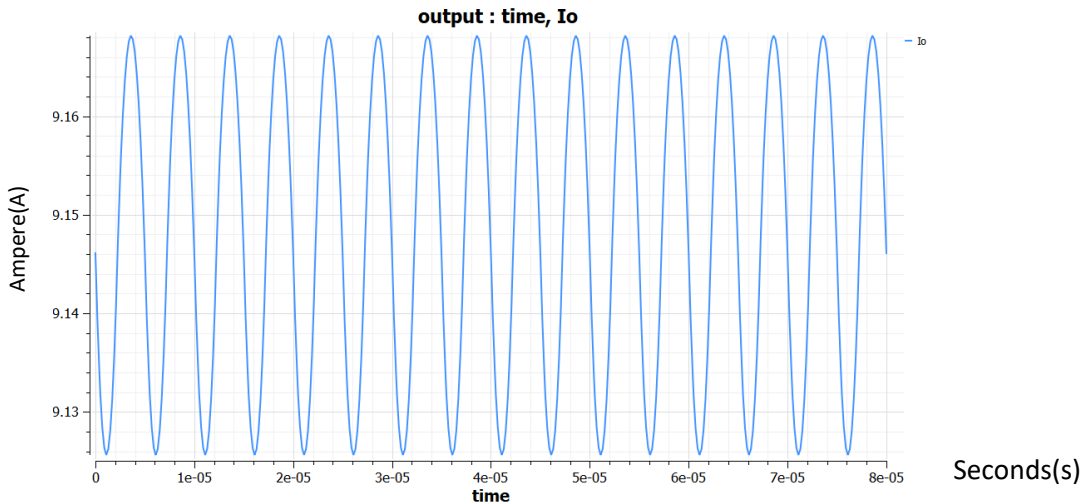


Figure 2: Output current vs time

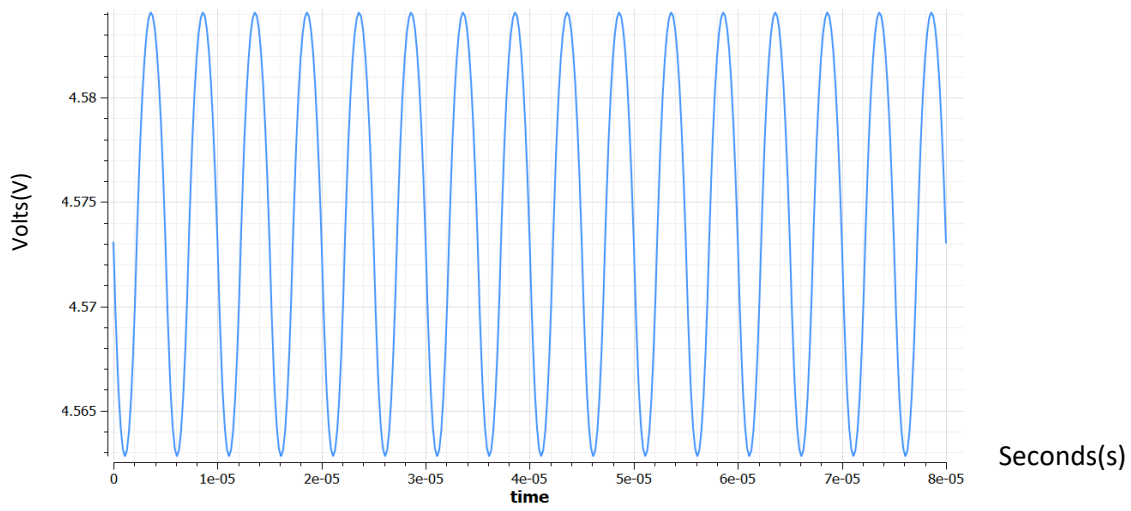


Figure 3:Output Voltage vs time

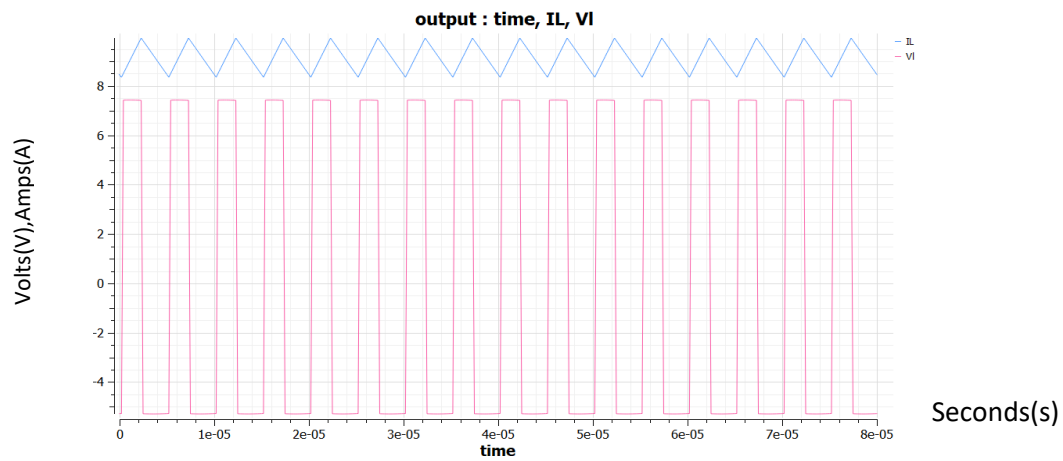


Figure 4:Inductor current, Inductor voltage vs time

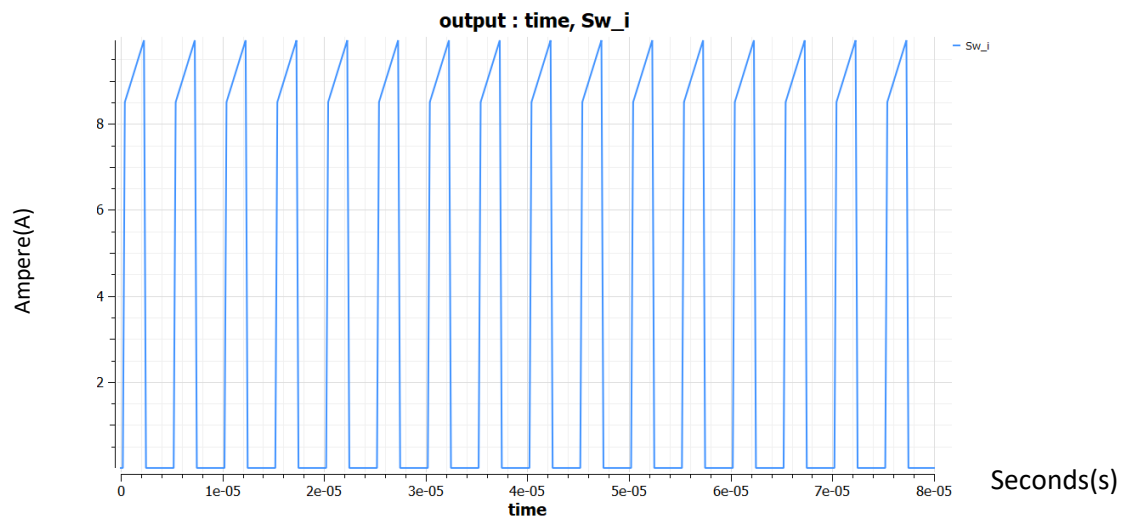


Figure 5: Switch current vs time

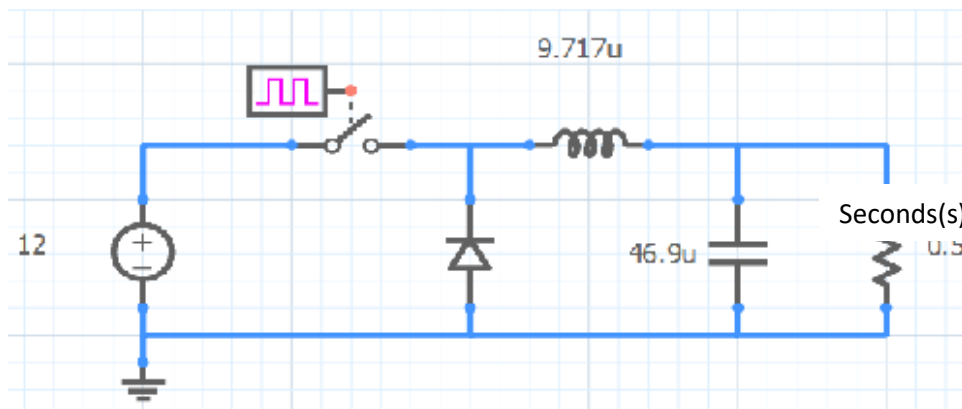


Figure 6: SEQUEL simulation circuit

Magnetics – Output filter inductor design

From the Power circuit equations, we get $L = 9.717 \mu\text{H}$ (12 A). The inductor is designed following [1].

Terms used in the following equations:-

1. Core Reluctance - \mathcal{R} (H^{-1})
2. Current Density - J (A/mm^2)
3. Wire size - a_w (m^2)
4. Effective length of core - l_e (mm)
5. Effective airgap length - l_g (mm)
6. Permeability of free space - μ_o (N/A^2)
7. Relative permeability - μ_r
8. Winding factor - k_w
9. Peak flux density - B_m (T)
10. Core Area - A_c (mm^2)
11. Window Area - A_w (mm^2)
12. Number of turns - N
13. Inductor rms current , peak current - I_{rms} (A), I_p (A)

Core Geometry – EE core

- Core Reluctance (\mathcal{R}) = $\frac{l_e}{\mu_o \mu_r A_c}$
- Total Reluctance (\mathcal{R}_{TOT}) = $\frac{l_e}{\mu_o \mu_r A_c} + \frac{l_g}{\mu_o A_c}$
- Wire size $a_w = \frac{I_{\text{rms}}}{J} \text{ m}^2$
- $LI = N A_c B_m = N \phi_p$
- $k_w A_w = N a_w = N I_{\text{rms}} / J$
- $k_w = 0.3-0.5$, $B_m = 0.2 \text{ T}$, $J = 3 \text{ A}/\text{mm}^2$.
- Required Air gap length = $l_g = \frac{\mu_o N I_p}{B_m}$
- Input L , I_p , I_{rms} , Wire Tables, Core Tables, J , B_m , k_w , f_{sw} (for choosing core material)

Assumptions:-

1. No Fringing : $l_g \ll \sqrt{A_c}$
2. Core Reluctance \ll Air gap reluctance, $\frac{l}{\mu_r} = l_g$

Effective core parameters

SYMBOL	PARAMETER	VALUE	UNIT
$\Sigma(l/A)$	core factor (C1)	0.850	mm^{-1}
V_e	effective volume	5590	mm^3
l_e	effective length	69.3	mm
A_e	effective area	80.7	mm^2
A_{min}	minimum area	80.7	mm^2
m	mass of core half	≈ 14	g

Figure 7:Core Parameters [6]

Inputs:-

Inputs				
S.No	Parameters	Symbol	Value	Unit
1	Inductance	L	10	uH
2	Flux Density	B	0.2	T
3	Peak current	I _p	15	A
4	RMS Current	I _{rms}	10.1	A
5	Current Density	J	3	A/mm ²
6	Window Factor	K _w	0.2	

$$\mu_0 = 12.57 * 10^{-7} \text{ Constant}$$

Calculations:-

Calculations				
	Calculated	Value	Unit	
	Ac * Aw	12625	mm ⁴	
	aw	3.37	mm ²	
From Core Table	Ac	80.7	mm ²	
	Aw	158.76	mm ²	
	MLT	67	mm	
From Wire Table	aw	3.243	mm ²	SWG
	Resistance/km	5.317	Ω/km	14
	New Ac*Aw	12811.93	mm ⁴	

Outputs:-

Outputs				
S.No	Parameters	Symbol	Value	Unit
1	No.of Turns	N	10	
2	Wire Size	a _w	3.243	mm ²
3	Air Gap (Core)	l _g	0.94275	mm
4	Wire Length	L	670	mm
5	Resistance	R	0.0035624	Ω
6	NewCurrent Density	J'	3.1144002	A/mm ²
7	New Window Factor	K _w '	0.204	

Losses in inductor and choosing core material:-

To compute the losses in the Inductor we see that there are two kinds of losses, namely:-

- 1) Copper Loss, $P_{Cu} = I_{rms}^2 \cdot R_{wire}$
- 2) Core Loss, P_{core}

R_{wire} is the resistance of wire used in winding the inductor.

$$R_{wire} = 5.317 \, \Omega/\text{km} \text{ (SWG 14)}$$

As per chosen wires, $P_{Cu} = 0.356 \text{ W}$.

Calculating AC flux density, we get 10mT, corresponding core loss is negligible.

Despite having very low value of AC flux density in the core, an iron core cannot be used here due to high switching frequency of 200 kHz, which would lead to large hysteresis losses.

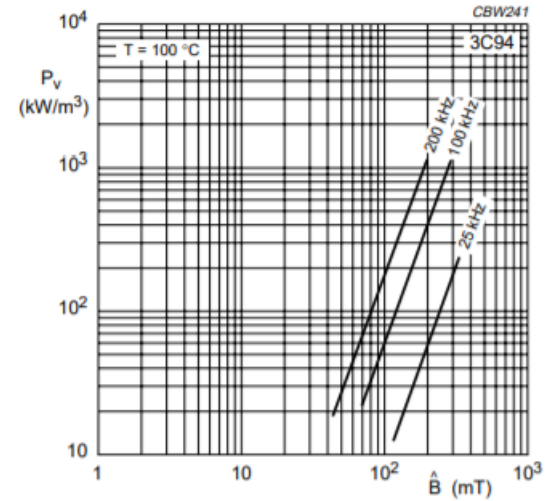


Figure 8:Core Loss[6]

Core Type – E34/14/9 [7]

Core Material Selected – 3C94 [7]

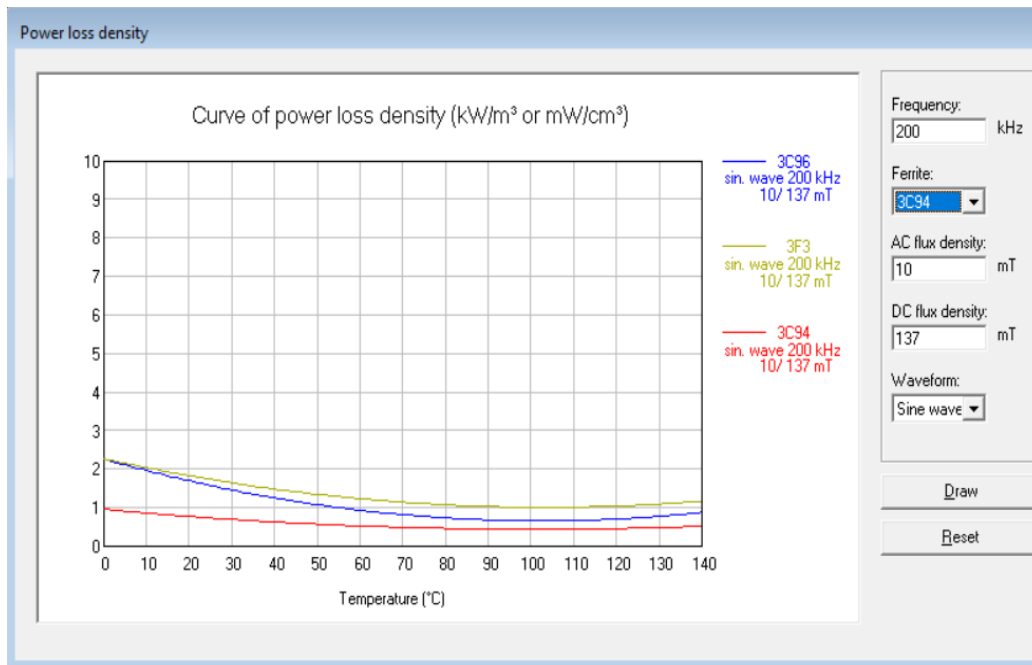


Figure 9: Comparison of Core Material Losses using Ferroxcube SFDT software ($B_m = 10\text{mT}$, $f_{sw} = 200\text{kHz}$) – [8]

Losses and efficiency:-

- Conduction Loss in MOSFET = $I_{sw(rms)}^2 R_{dson}$
- Conduction Loss in Diode = $I_o * V_F * (1-D)$, V_F = forward bias voltage
- Switching loss = $0.5 * V_g * I_o * (t_r + t_f) * f_{sw}$, t_r, t_f – rise and fall times
- Inductor Loss = $P_{Cu} + P_{core}$
- Operation loss by IC = $V_g * I_{cc}$ ($I_{cc}=1mA$, current drawn by IC- SG3524)
- Power Loss in output Capacitor = $I_c^2 * ESR$, (I_c – Capacitor RMS current)

∴ the computed losses are as follows:-

- ❑ The diode loss = 6.45 W (**Dominant**)
- ❑ MOSFET conduction loss = 5.6 W
- ❑ Switching Loss = 0.504 W
- ❑ Inductor Loss = 0.356 W
- ❑ IC operation Loss = 0.012 W
- ❑ Capacitor Loss = 0.01 W

$$\text{Efficiency} = \frac{\text{Output Power}}{\text{Input Power}}$$

- Output Power = 50 W
- Input Power = 61 W

$$\text{Efficiency} = 81.92\%$$

Improving the efficiency: -

- Efficiency can be improved by using different MOSFET with lower R_{dson} (i.e $< 0.15 \Omega$)
- Diode loss can be substantially reduced by opting for synchronous buck converter

1.1 Closed Loop Control:-

The main objective here is to have a steady DC output of 5V. In order to do this, we use the voltage mode control of the output, so that the duty ratio is adjusted so as to maintain constant output voltage. Frequency domain parameters are used to analyze and design the feedback circuit.

1.1.a Small Signal Analysis :-

We derive the transfer function of the non-ideal buck converter, considering R_{ds-on} MOSFET on-state resistance, ESR of Capacitor- r_c , ESR of inductor r_l .

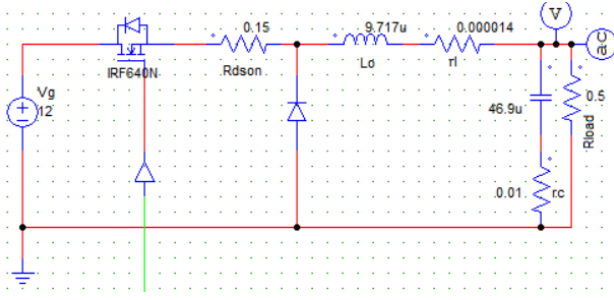


Figure 10: Nonideal buck converter power circuit

$r_l = \text{Length of wire} * R_{\text{wire}} = \text{Number of Turns (N)} * \text{Mean Length per turn (MLT)} * R_{\text{wire}}$

$$r_l = 14 \mu\Omega$$

IRF640N on-state resistance $R_{dson} = 0.15 \Omega$

$$r_c = 10 \text{ m}\Omega$$

Load resistance $R \gg r_c + r_l + R_{ds-on}$

$$\text{Expression for Duty ratio } D_p = \frac{V_o(R+r_l)}{V_o * R_{dson} + R * V_g} \quad \text{----- Eqn.1}$$

$$\text{Final Transfer function } G_{vd}(s) = \frac{R(V_g + I_l(-R_{dson})) * (1 + sC * r_c)}{\Delta(s)} \quad \text{where } \Delta(s) \text{ is}$$

$$\Delta(s) = s^2 LCR + s[L + RC\{r_c + r_l + D_p(R_{dson})\} + r_c C\{D_p(R_{dson}) + r_l\}] + R + D_p(R_{dson} + 2 * r_l)]$$

-----Eqn.2

Thus, we see that the transfer function is a second-order system with complex pole pair.

$$\text{Here, } \omega_o = \sqrt{\frac{R + D_p(R_{dson} + 2 * r_l)}{LCR}}$$

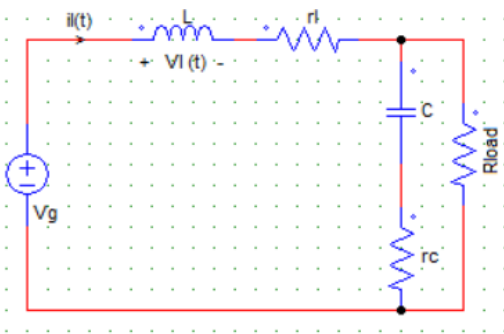


Figure 11: Switch ON state

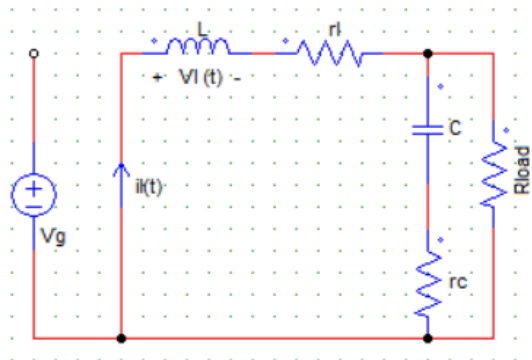


Figure 12: Switch OFF state

Controller design: -

Parameters: Steady state error (<1%), permissible transient overshoot (<5%), settling time.

Following Section 6.2.2 – [1],

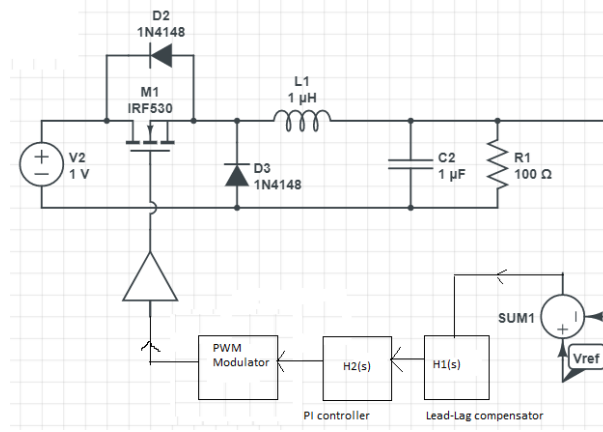


Figure 13: Controller Block diagram

We design the compensator with two blocks cascaded. $H_1(s)$ achieves desired bandwidth and phase margin, $H_2(s)$ reduces the steady state error.

Thus $H_1(s)$ is a lead-lag compensator –

$$H_1(s) = K_1 \frac{1 + \frac{s}{\omega_{z1}}}{1 + \frac{s}{\omega_{p1}}}$$

$H_2(s)$ is designed so that it does not affect the phase margin and gain margin already designed.

$H_2(s)$ is a PI controller -

$$H_2(s) = \frac{1 + \frac{s}{\omega_{z2}}}{\frac{s}{\omega_{z2}}}$$

Overall compensator transfer function is

$$H(s) = K_1 \frac{1 + \frac{s}{\omega_{z1}}}{1 + \frac{s}{\omega_{p1}}} \frac{1 + \frac{s}{\omega_{z2}}}{\frac{s}{\omega_{z2}}}$$

For acceptable transient overshoot, the phase margin must be greater than 45° . Due to the complex pole pair of $G_{vd}(s)$, $\omega_{z1} = \omega_0$, $\omega_{p1} = 10 * \omega_{z1}$. K_1 is adjusted to get required phase margin at the desired crossover frequency. **$K_1 = 0.25$** .

$$\therefore H_1(s)H_2(s) = K_1 * \frac{1 + \frac{s}{49378}}{1 + \frac{s}{493780}} * \frac{1 + \frac{s}{5000}}{\frac{s}{5000}} = \frac{5.063 * 10^{-6} s + 0.25}{2.025 * 10^{-6} s + 1} * \frac{0.0002s + 1}{0.0002s}$$

Symbols used above: -

1. ω_{z1}, ω_{p1} = Zero, pole of $H_1(s)$ transfer function (Lead -lag compensator)
2. ω_{z2} = Zero of PI Controller $H_2(s)$
3. K_1 = Constant

Results: -

- Final phase margin $\phi_m = 79.81^\circ$
- Gain margin = infinite

- Gain crossover frequency $\omega_c = 2.06 \times 10^4$ rad/s or $f_c = 3278.59$ Hz

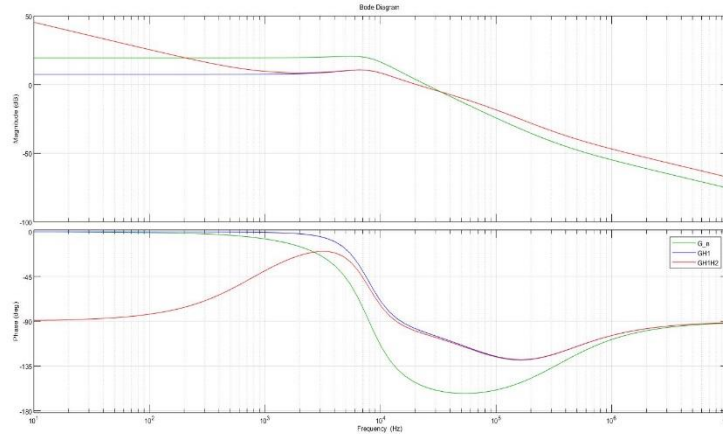
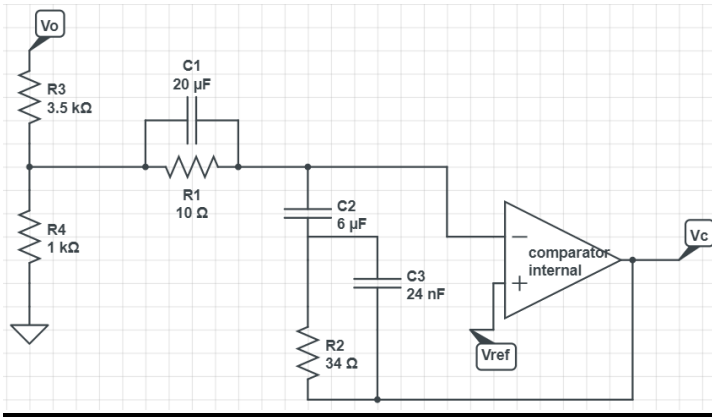


Figure 14: Bode Plot of closed loop buck converter

Circuit components:-



Component	Value
R1	10 Ω
R2	33.3 Ω
R3	3.5 k Ω
R4	1 k Ω
C1	20 μ F
C2	6 μ F
C3	24 nF

Figure 15: Closed loop control circuit

$$Z_2 = (R_2 + \frac{1}{sC_2}) \parallel (\frac{1}{sC_3}) = \frac{1+sR_2C_2}{s(C_2+C_3)(\frac{1+sR_2C_2C_3}{C_3+C_2})}, \quad Z_1 = R_1 \parallel \frac{1}{sC_1} = \frac{R_1}{1+sR_1C_1} \quad \text{----- Eqn.3}$$

$$\omega_{z2} = 1/R_2C_2 = 5000, \quad R_2C_2 = 0.0002 \quad \text{----- Eqn.4}$$

$$\omega_{z1} = 1/R_1C_1 = 49378, \quad R_1C_1 = 2.025 \times 10^{-5} \quad \text{----- Eqn.5}$$

$$V_c = V_{ref} (1 + \frac{Z_2}{Z_1}) - V_x (\frac{Z_2}{Z_1}) = 1.1112 \text{ V}, \quad (V_x = V_{ref} = 3 \text{ V}) \quad \text{----- Eqn.6}$$

$$K = \frac{R_4}{3(R_3+R_4)} * \frac{R_2C_2}{R_1(C_2+C_3)} \quad \text{----- Eqn.7}$$

$$\omega_{p1} = \frac{C_2+C_3}{R_2 * C_2 * C_3} \quad \text{----- Eqn.8}$$

Using these above equations, the component values are determined.

Resonant Converter:-

ZCS Converter:-

The closed loop buck converter can now be converted into a resonant converter, first one being Zero-Current Switching type. Gate pulse is high until switch current $i_s(t)$ reverses polarity, at which point, the MOSFET (M) body diode will conduct. Now gate pulse is removed. M will turn off at $i_s(t)$ zero-crossing from negative to positive.

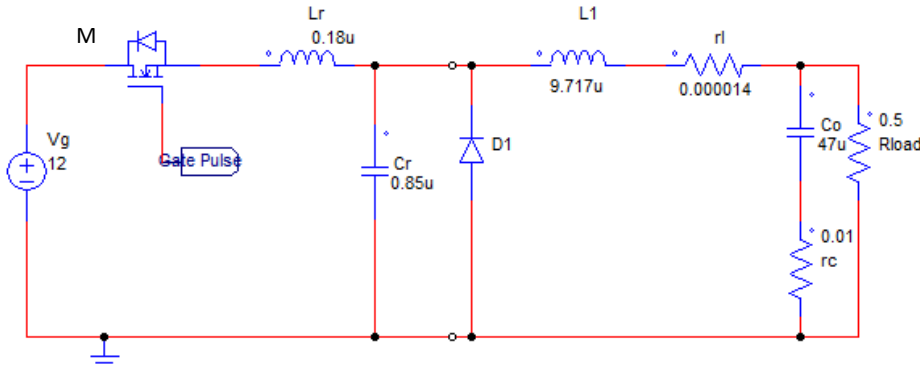


Figure 16: ZCS Buck converter power circuit

Calculations:-

Input: $V_g = 12\text{ V}$, $V_o = 5\text{ V}$, $I_o = 10\text{ A}$, $f_{sw} = 200\text{ kHz}$

L_r , C_r are the resonant inductance and capacitance respectively.

Q – Quality factor

\therefore Let $M_f = V_o/V_g = 0.416$

$$Q = \omega_o R C_r = R/Z_0, \text{ where } Z_0 = \sqrt{\frac{L_r}{C_r}}$$

$$M_f = G_f(\sigma) \frac{f_{sw}}{f_o} \text{ where } G_f(\sigma) \text{ is practically constant} = 1.$$

So conversion factor of the converter can be taken as $M_f = \frac{f_{sw}}{f_o}$.

$$\therefore f_o = 480.769\text{ kHz} = 481\text{ kHz}$$

$$\omega_o = 2\pi f_o = 2\sqrt{\frac{L_r}{C_r}} = 3022.21 * 10^3 \text{ rad/s} \quad L_r = \frac{Z_o}{\omega_o}, C_r = \frac{1}{Z_o \omega_o}$$

$$\text{Let } \sigma = \frac{I_o}{V_g} * \sqrt{\frac{L_r}{C_r}}, \text{ a dimensionless parameter.} \quad \text{----- Eqn.9}$$

For successful ZCS switching, source current must have a zero-crossing.

$$\therefore i_s(t) = I_o + V_g * \sqrt{\frac{C_r}{L_r}} * \sin(\omega_o t) = 0$$

$$\text{or, } i_s(t) = I_o(1 + \frac{1}{\sigma} \sin(\omega_o t)) = 0 \quad \text{----- (Using Eqn.9)}$$

$$\therefore I_o \leq V_g^* \sqrt{\frac{C_r}{L_r}} \text{ or } \sigma \leq 1$$

Choosing $L_r = 0.18 \text{ uH}$ (31 A), $C_r = 0.9 \text{ uF}$ (10 V), we get $\sigma = 0.3762$.

Verification by PSIM simulation:-

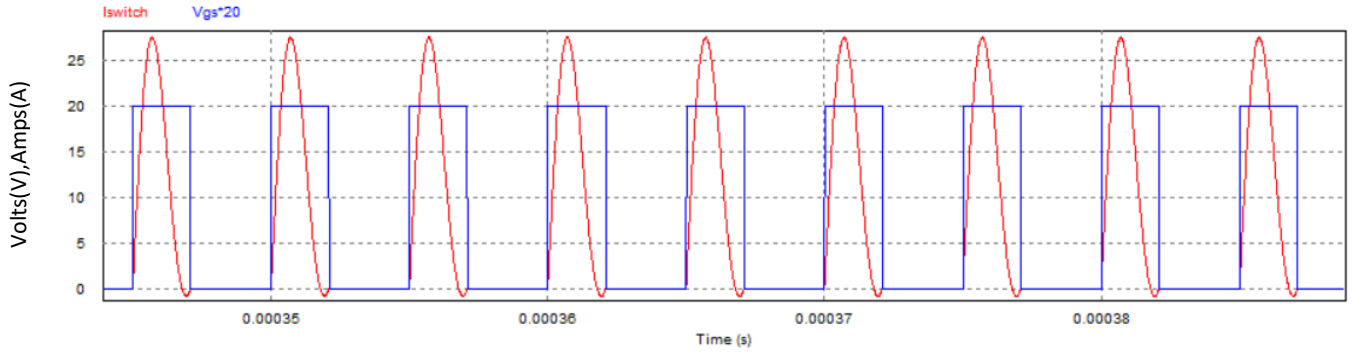


Figure 17: ZCS Switching action (I_{sw} , V_{gs} vs time)

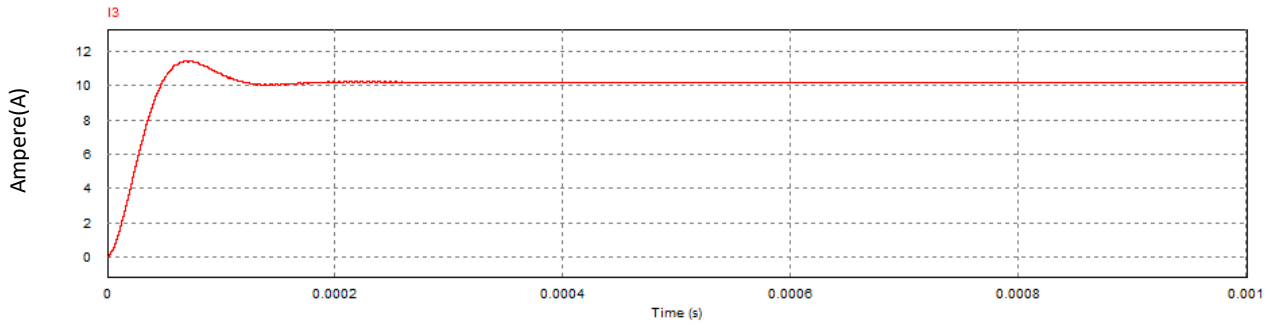


Figure 18: Output current 10A

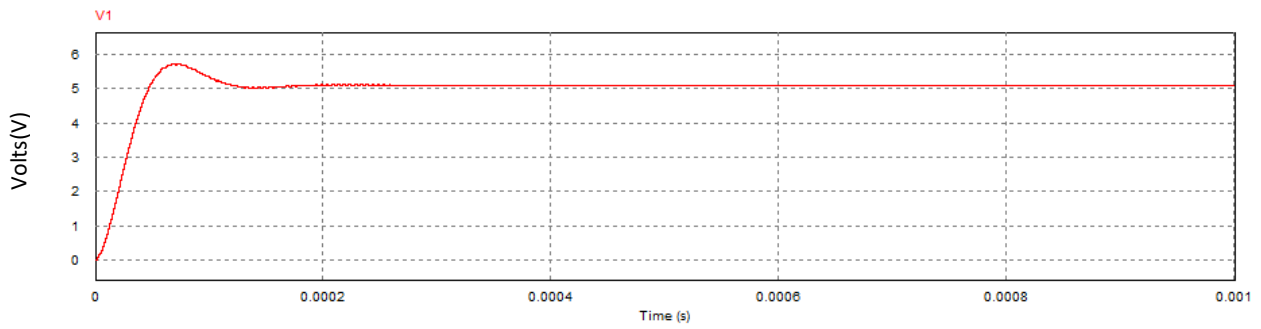


Figure 19: Output Voltage 5V

ZVS (Zero-Voltage Switching): -

The dual of the ZCS type is the ZVS action. Resonance determines the off-time here.

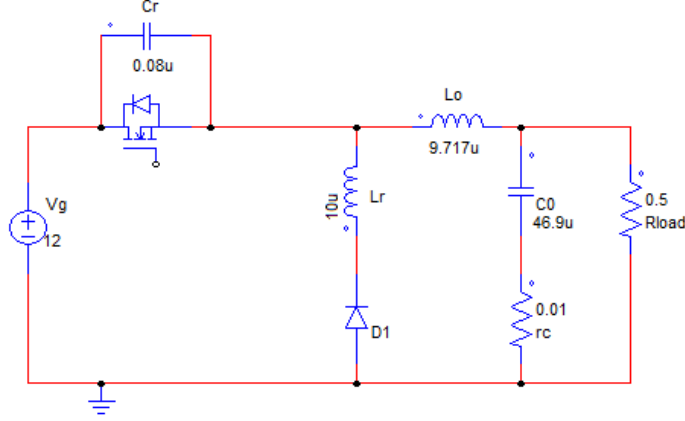


Figure 20: ZVS Buck Converter Power circuit

$$V_g - v_t(t) - L_r \frac{di_s}{dt} = 0 \quad \text{---- Eqn.10}$$

$$v_c(t) = C_r \frac{dv_t}{dt} = i_s + I_o \quad \text{---- Eqn.11}$$

$$\text{Solving, we get } v_c(t) = V_g + I_o Z_o \sin(\omega_o t) \quad \text{---- Eqn.12}$$

Let $\sigma = \frac{I_o}{V_g} * \sqrt{\frac{L_r}{C_r}}$, a dimensionless parameter.

$$\text{Rewriting Eqn.12, } v_c(t) = V_g (1 + \sigma * \sin(\omega_o t)) \quad \text{---- Eqn.13}$$

Thus from Eqn.13, it can be seen that for ZVS action, $\sigma \geq 1$.

Choosing $L_r = 10 \text{ uH}$ (4 A), $C_r = 0.08 \text{ uF}$ (40 V), we get $\sigma = 9.3169$.

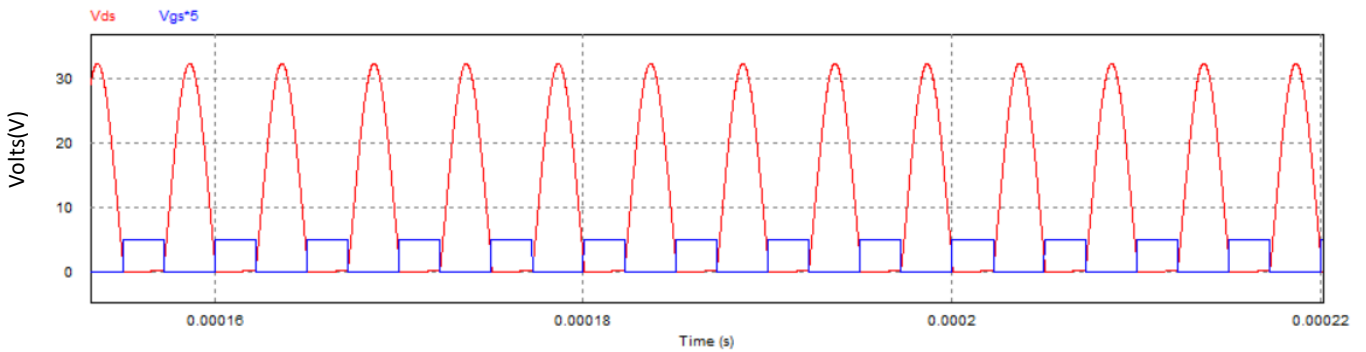


Figure 21: $V_{ds}, V_{gs} * 5$ vs time, ZVS switching action

Gate driver - UCC5304DWVR – Texas Instruments

The UCC5304 device is an isolated single-channel gate driver with 4 A peak source and 6 A peak sink current. It has been used here to drive the MOSFET – IRF640N. Using this IC from Texas Instruments obviated providing isolation between the gate driver circuit and power circuit separately with the use of pulse-transformer or optical isolation. Since the input of UCC5304 is isolated from the output drivers, the input signal amplitude can be larger than VDD (within recommended limit).

- Pin 1 is supplied from SG3524 through an inverter.
- Pin 8, VDD, is given +18 V isolated supply.
- Pin 5,6 grounded.
- Pins 2,3 given a +5 V supply using L7805 regulator.

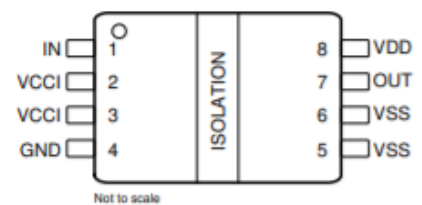


Figure 22: Pin configuration [9]

- Pin 7, OUT pin is fed to the gate terminal of IRF640N through 22 Ω resistors.

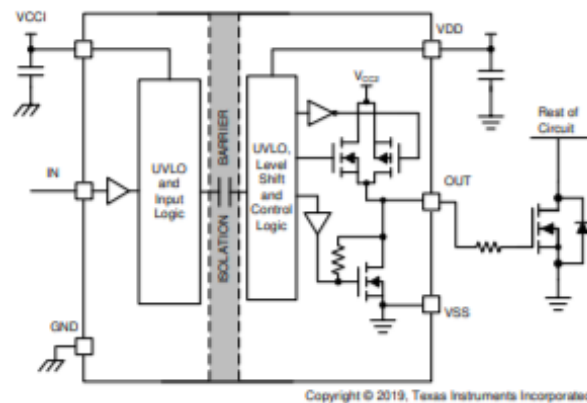
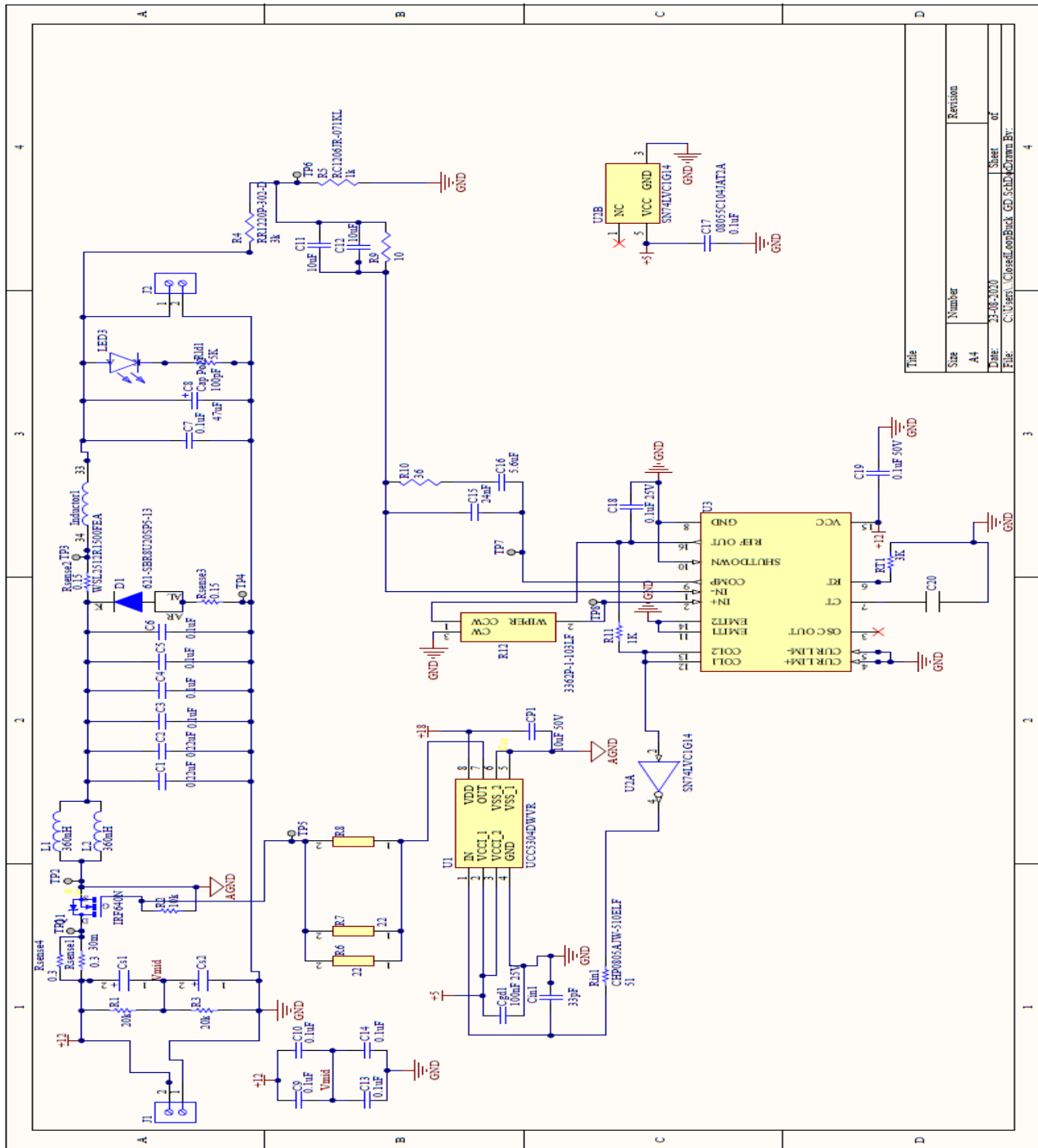


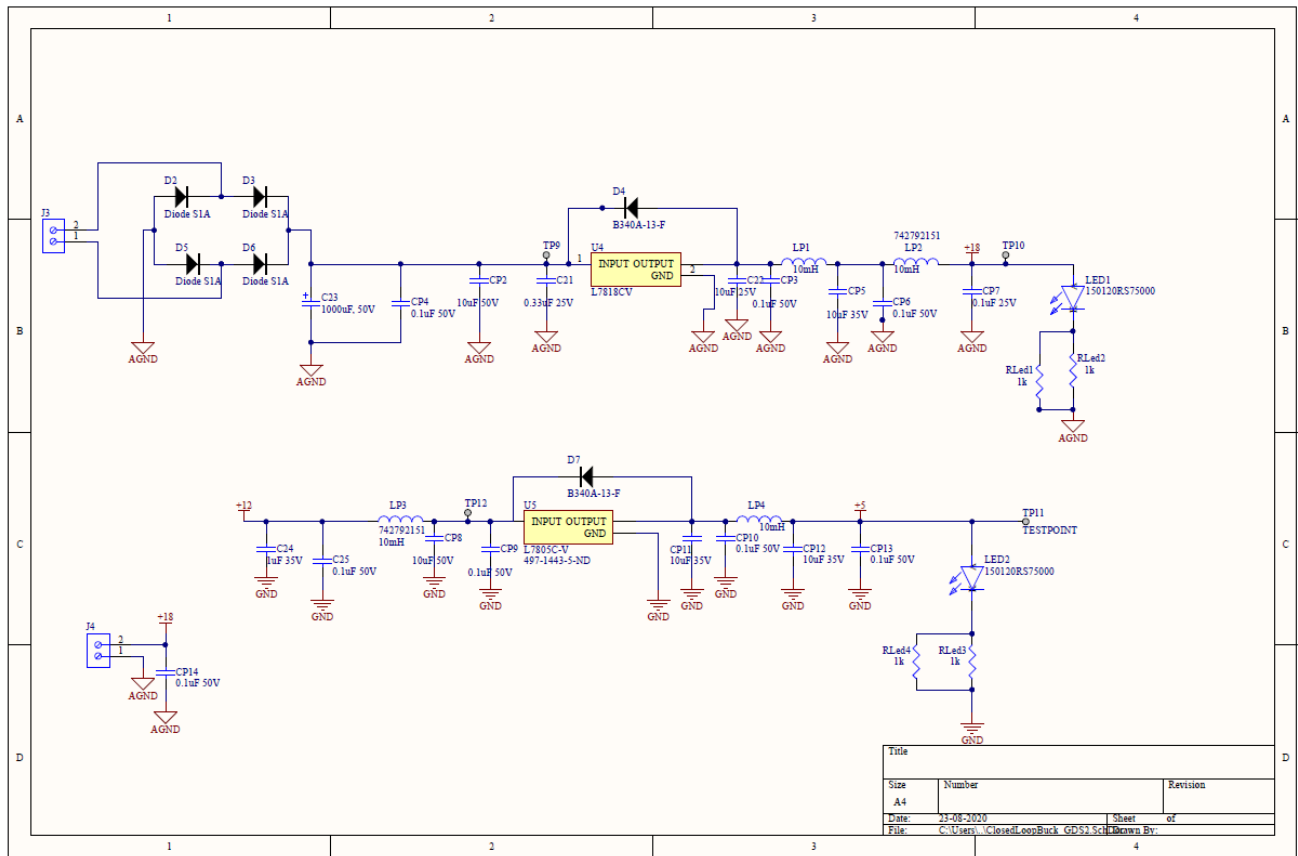
Figure 23: Typical application [9]

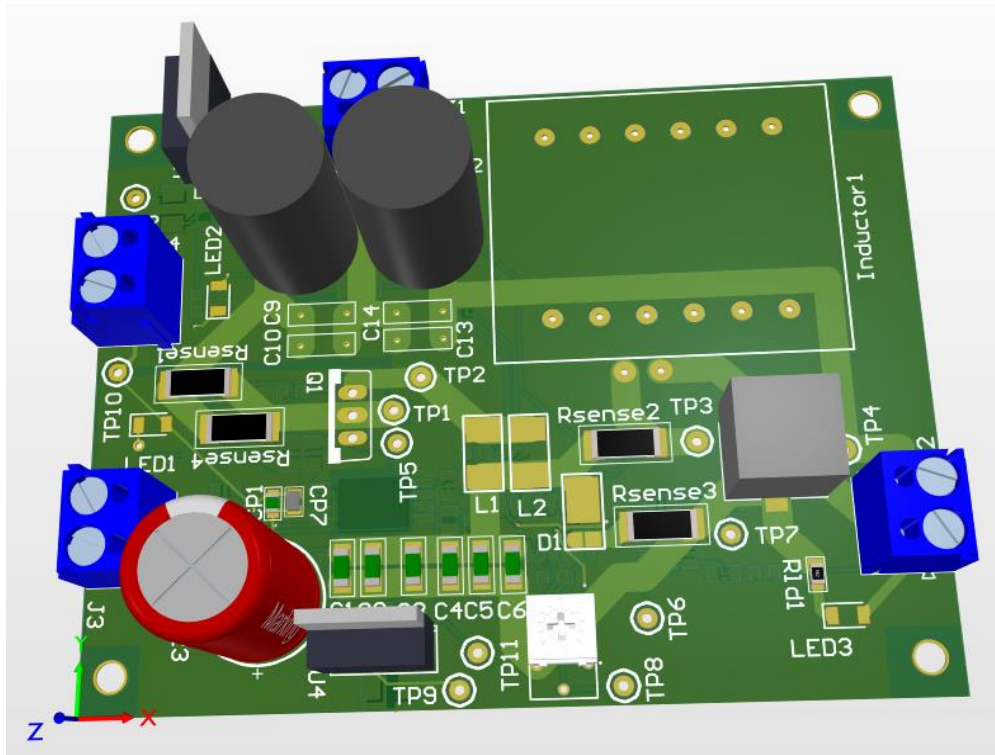
- 50 V, 10 μ F MLCC and 50 V, 220 nF MLCC are chosen for C_{VDD} (refer. Figure 23).
- Bypass capacitor connected to pins 2,3 is a 25 V, 100 nF MLCC.
- $R_{IN} = 51 \Omega$, $C_{IN} = 33$ pF are chosen following recommendations in datasheet. [9]

Altium Schematic:-



Schematic page 2





References:-

- [1] Course Material on Switched-Mode Power Supply by V.Ramanarayanan
- [2] Power Electronics – Ned Mohan, Tore M.Undeland, William P.Robbins
- [3] Elements of Power Electronics – Philip T.Krein
- [4] Fundamentals of MOSFET and IGBT Gate Driver Circuits by Lazlo Balogh – Application Note, Texas Instruments
- [5] MOSFET Gate Drive circuit – Toshiba – Application Note - 20180726
- [6] Datasheet –
- [9] Datasheet - UCC5304DWR Texas Instruments